## PROCEEDINGS OF SPIE

# Novel In-Plane Semiconductor Lasers XX

Alexey A. Belyanin Peter M. Smowton Editors

6–11 March 2021 Online Only, United States

Sponsored and Published by SPIE

Volume 11705

Proceedings of SPIE 0277-786X, V. 11705

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Author(s), "Title of Paper," in Novel In-Plane Semiconductor Lasers XX, edited by Alexey A. Belyanin, Peter M. Smowton, Proceedings of SPIE Vol. 11705 (SPIE, Bellingham, WA, 2021) Seven-digit Article CID Number.

ISSN: 0277-786X ISSN: 1996-756X (electronic)

ISBN: 9781510642454 ISBN: 9781510642461 (electronic)

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